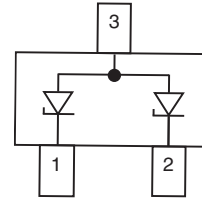


**Features**

- Two-line ESD protection device
- ESD immunity acc. IEC 61000-4-2  
± 30 kV contact discharge  
± 30 kV air discharge
- ESD capability according to AEC-Q101:  
human body model: class H3B: > 8 kV
- Space saving SOT-23 package
- AEC-Q101 qualified available



**ABSOLUTE MAXIMUM RATINGS GSOT03C**

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	30	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		30	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	369	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		504	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	± 30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		± 30	kV
Operating temperature	Junction temperature	$T_J$	-55 to +150	°C
Storage temperature		$T_{STG}$	-55 to +150	°C

**ABSOLUTE MAXIMUM RATINGS GSOT04C**

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	30	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		30	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	429	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		564	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	-55 to +150	$^{\circ}C$
Storage temperature		$T_{STG}$	-55 to +150	$^{\circ}C$

**ABSOLUTE MAXIMUM RATINGS GSOT05C**

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	30	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		30	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	480	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		612	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	-55 to +150	$^{\circ}C$
Storage temperature		$T_{STG}$	-55 to +150	$^{\circ}C$

**ABSOLUTE MAXIMUM RATINGS GSOT08C**

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	18	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		18	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	345	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		400	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	-55 to +150	$^{\circ}C$
Storage temperature		$T_{STG}$	-55 to +150	$^{\circ}C$

**ABSOLUTE MAXIMUM RATINGS GSOT12C**

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	12	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		12	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	312	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		337	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	-55 to +150	$^{\circ}C$
Storage temperature		$T_{STG}$	-55 to +150	$^{\circ}C$

**ABSOLUTE MAXIMUM RATINGS GSOT15C**

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	8	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		8	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	345	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		400	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	-55 to +150	$^{\circ}C$
Storage temperature		$T_{STG}$	-55 to +150	$^{\circ}C$

**ABSOLUTE MAXIMUM RATINGS GSOT24C**

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	5	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		5	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	235	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		240	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	-55 to +150	$^{\circ}C$
Storage temperature		$T_{STG}$	-55 to +150	$^{\circ}C$

**ABSOLUTE MAXIMUM RATINGS GSOT36C**

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$I_{PPM}$	3.5	A
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		3.5	A
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	$P_{PP}$	248	W
	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot		252	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	$\pm 30$	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		$\pm 30$	kV
Operating temperature	Junction temperature	$T_J$	-55 to +150	$^{\circ}C$
Storage temperature		$T_{STG}$	-55 to +150	$^{\circ}C$

**BiAs-MODE** (2-line Bidirectional Asymmetrical protection mode)

With the GSOTxxC two signal- or data-lines (L1, L2) can be protected against voltage transients. With pin 3 connected to ground and pin 1 and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified Maximum Reverse Working Voltage ( $V_{RWM}$ ) the protection diode between pin 2 and pin 3 and between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The Clamping Voltage ( $V_C$ ) is defined by the breakdown voltage ( $V_{BR}$ ) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low Forward Voltage ( $V_F$ ) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the GSOTxxC clamping behavior is Bidirectional and Asymmetrical (BiAs).

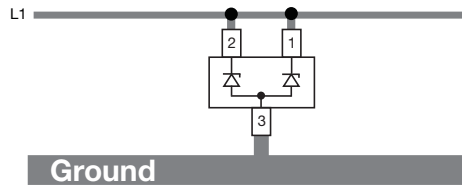


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If a higher surge current or peak pulse current ( $I_{PP}$ ) is needed, both protection diodes in the GSOTxxC can also be used in parallel in order to “double” the performance.

This offers:

- double surge power = double peak pulse current ( $2 \times I_{PPM}$ )
- half of the line inductance = reduced clamping voltage
- half of the line resistance = reduced clamping voltage
- double line capacitance ( $2 \times C_D$ )
- double reverse leakage current ( $2 \times I_R$ )



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**ELECTRICAL CHARACTERISTICS GSOT03C** ( $T_{amb} = 25\text{ °C}$  unless otherwise specified)  
between pin 1 to pin 3 or pin 2 to pin 3

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			2	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			3.3	V
Reverse voltage	at $I_R = 100\ \mu A$	$V_R$	3.3			V
Reverse current	at $V_R = 3.3\ V$	$I_R$			10	0 $\mu A$
Reverse breakdown voltage	at $I_R = 1\ mA$	$V_{BR}$	4.0	4.6	5.5	V
Reverse clamping voltage	at $I_{PP} = 1\ A$	$V_C$		5.7	7.5	V
	at $I_{PP} = I_{PPM} = 30\ A$			10	12.3	V
Forward clamping voltage	at $I_{PP} = 1\ A$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 30\ A$			4.5		V
Capacitance	at $V_R = 0\ V$ ; $f = 1\ MHz$	$C_D$		420	600	pF
	at $V_R = 1.6\ V$ ; $f = 1\ MHz$			260		pF

**ELECTRICAL CHARACTERISTICS GSOT04C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 3 or pin 2 to pin 3

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			2	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			4	V
Reverse voltage	at $I_R = 20\text{ }\mu\text{A}$	$V_R$	4			V
Reverse current	at $V_R = 4\text{ V}$	$I_R$			20	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	5	6.1	7	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		7.5	9	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$			11.2	14.3	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$			4.5		V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		310	450	pF
	at $V_R = 2\text{ V}; f = 1\text{ MHz}$			200		pF

**ELECTRICAL CHARACTERISTICS GSOT05C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 3 or pin 2 to pin 3

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			2	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			5	V
Reverse voltage	at $I_R = 10\text{ }\mu\text{A}$	$V_R$	5			V
Reverse current	at $V_R = 5\text{ V}$	$I_R$			10	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	6	6.8	8	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		7	8.7	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$			12	16	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$			4.5		V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		260	350	pF
	at $V_R = 2.5\text{ V}; f = 1\text{ MHz}$			150		pF

**ELECTRICAL CHARACTERISTICS GSOT08C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 3 or pin 2 to pin 3

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			2	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			8	V
Reverse voltage	at $I_R = 5\text{ }\mu\text{A}$	$V_R$	8			V
Reverse current	at $V_R = 8\text{ V}$	$I_R$			5	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	9	10	11	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		10.7	13	V
	at $I_{PP} = I_{PPM} = 18\text{ A}$			15.2	19.2	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 18\text{ A}$			3		V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		160	250	pF
	at $V_R = 4\text{ V}; f = 1\text{ MHz}$			80		pF

**ELECTRICAL CHARACTERISTICS GSOT12C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 3 or pin 2 to pin 3

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			2	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			12	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	$V_R$	12			V
Reverse current	at $V_R = 12\text{ V}$	$I_R$			1	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	13.5	15	16.5	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		15.4	18.7	V
	at $I_{PP} = I_{PPM} = 12\text{ A}$			21.2	26	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 12\text{ A}$			2.2		V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		115	150	pF
	at $V_R = 6\text{ V}; f = 1\text{ MHz}$			50		pF

**ELECTRICAL CHARACTERISTICS GSOT15C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 3 or pin 2 to pin 3

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			2	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			15	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	$V_R$	15			V
Reverse current	at $V_R = 15\text{ V}$	$I_R$		1		$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	16.5	18	20	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		19.4	23.5	V
	at $I_{PP} = I_{PPM} = 8\text{ A}$			24.8	28.8	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 8\text{ A}$			1.8		V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		90	120	pF
	at $V_R = 7.5\text{ V}; f = 1\text{ MHz}$			35		pF

**ELECTRICAL CHARACTERISTICS GSOT24C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 3 or pin 2 to pin 3

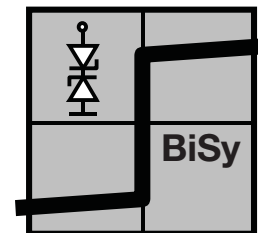
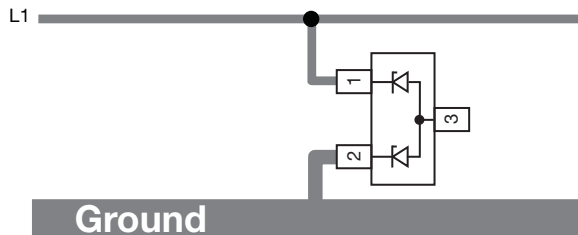
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			2	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			24	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	$V_R$	24			V
Reverse current	at $V_R = 24\text{ V}$	$I_R$			1	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	27	30	33	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		34	41	V
	at $I_{PP} = I_{PPM} = 5\text{ A}$			41	47	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 5\text{ A}$			1.4		V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		65	80	pF
	at $V_R = 12\text{ V}; f = 1\text{ MHz}$			20		pF

**ELECTRICAL CHARACTERISTICS GSOT36C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
between pin 1 to pin 3 or pin 2 to pin 3

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			2	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			36	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	$V_R$	36			V
Reverse current	at $V_R = 36\text{ V}$	$I_R$			1	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	39	43	47	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		49	60	V
	at $I_{PP} = I_{PPM} = 3.5\text{ A}$			59	71	V
Forward clamping voltage	at $I_{PP} = 1\text{ A}$	$V_F$		1	1.2	V
	at $I_{PP} = I_{PPM} = 3.5\text{ A}$			1.3		V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		52	65	pF
	at $V_R = 18\text{ V}; f = 1\text{ MHz}$			12		pF

**BiSy-MODE** (1-line bidirectional symmetrical protection mode)

If a bipolar symmetrical protection device is needed the GSOTxxC can also be used as a single line protection device. Therefore pin 1 has to be connected to the signal- or data-line (L1) and pin 2 to ground (or vice versa). Pin 3 must not be connected. Positive and negative voltage transients will be clamped in the same way. The clamping current through the GSOTxxC passes one diode in forward direction and the other one in reverse direction. The clamping voltage ( $V_C$ ) is defined by the breakthrough voltage ( $V_{BR}$ ) level of one diode plus the forward voltage of the other diode plus the voltage drop at the series impedances (resistances and inductances) of the protection device. Due to the same clamping levels in positive and negative direction the GSOTxxC voltage clamping behaviour is bidirectional and symmetrical (BiSy).



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**ELECTRICAL CHARACTERISTICS GSOT03C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			1	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			3.8	V
Reverse voltage	at $I_R = 100\text{ }\mu\text{A}$	$V_R$	3.8			V
Reverse current	at $V_R = 3.8\text{ V}$	$I_R$			100	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	4.5	5.3	6.2	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		7	8.4	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$			14	16.8	V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		210	300	pF
	at $V_R = 1.6\text{ V}; f = 1\text{ MHz}$			190		pF



**ELECTRICAL CHARACTERISTICS GSOT04C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			1	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			4.5	V
Reverse voltage	at $I_R = 20\text{ }\mu\text{A}$	$V_R$	4.5			V
Reverse current	at $V_R = 4.5\text{ V}$	$I_R$			20	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	5.5	6.8	7.7	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		7.5	9	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$			15.7	18.8	V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		155	225	pF
	at $V_R = 2\text{ V}; f = 1\text{ MHz}$			135		pF

**ELECTRICAL CHARACTERISTICS GSOT05C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			1	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			5.5	V
Reverse voltage	at $I_R = 10\text{ }\mu\text{A}$	$V_R$	5.5			V
Reverse current	at $V_R = 5.5\text{ V}$	$I_R$			10	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	6.5	7.5	8.7	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		8.1	9.7	V
	at $I_{PP} = I_{PPM} = 30\text{ A}$			17	20.4	V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		130	175	pF
	at $V_R = 4\text{ V}; f = 1\text{ MHz}$			100		pF

**ELECTRICAL CHARACTERISTICS GSOT08C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			1	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			8.5	V
Reverse voltage	at $I_R = 5\text{ }\mu\text{A}$	$V_R$	8.5			V
Reverse current	at $V_R = 8.5\text{ V}$	$I_R$			5	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	9.5	10.7	11.7	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		11.7	14	V
	at $I_{PP} = I_{PPM} = 18\text{ A}$			18.5	22.2	V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		80	125	pF
	at $V_R = 4\text{ V}; f = 1\text{ MHz}$			60		pF

**ELECTRICAL CHARACTERISTICS GSOT12C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			1	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			12.5	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	$V_R$	12.5			V
Reverse current	at $V_R = 12.5\text{ V}$	$I_R$			1	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	13.5	15.7	16.5	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		16.4	19.7	V
	at $I_{PP} = I_{PPM} = 12\text{ A}$			23.4	28.1	V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		58	75	pF
	at $V_R = 7.5\text{ V}; f = 1\text{ MHz}$			36		pF

**ELECTRICAL CHARACTERISTICS GSOT15C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			1	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			15.5	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	$V_R$	15.5			V
Reverse current	at $V_R = 15.5\text{ V}$	$I_R$			1	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	17	18.7	20.7	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		20.4	24.5	V
	at $I_{PP} = I_{PPM} = 8\text{ A}$			26.6	30.6	V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		45	60	pF
	at $V_R = 7.5\text{ V}; f = 1\text{ MHz}$			25		pF

**ELECTRICAL CHARACTERISTICS GSOT24C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			1	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			24.5	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	$V_R$	24.5			V
Reverse current	at $V_R = 24.5\text{ V}$	$I_R$			1	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	27.5	30.7	33.7	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		34	41	V
	at $I_{PP} = I_{PPM} = 5\text{ A}$			40	48	V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		33	40	pF
	at $V_R = 12\text{ V}; f = 1\text{ MHz}$			18		pF

**ELECTRICAL CHARACTERISTICS GSOT36C** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)  
 between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	$N_{channel}$			1	lines
Reverse stand-off voltage	Max. reverse working voltage	$V_{RWM}$			36.5	V
Reverse voltage	at $I_R = 1\text{ }\mu\text{A}$	$V_R$	36.5			V
Reverse current	at $V_R = 36.5\text{ V}$	$I_R$			1	$\mu\text{A}$
Reverse breakdown voltage	at $I_R = 1\text{ mA}$	$V_{BR}$	39.5	43.7	47.7	V
Reverse clamping voltage	at $I_{PP} = 1\text{ A}$	$V_C$		50	60	V
	at $I_{PP} = I_{PPM} = 3.5\text{ A}$			60	72	V
Capacitance	at $V_R = 0\text{ V}; f = 1\text{ MHz}$	$C_D$		26	33	pF
	at $V_R = 18\text{ V}; f = 1\text{ MHz}$			10		pF

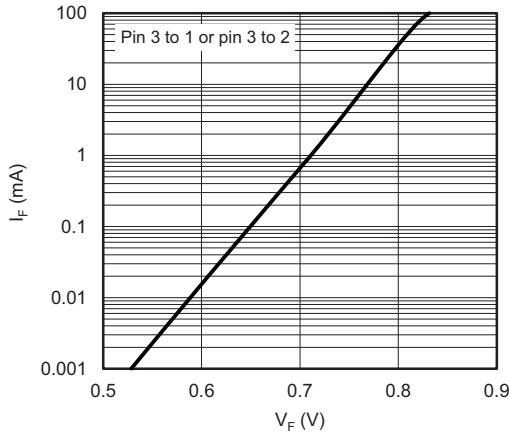


Fig. 1 - Typical Forward Current  $I_F$  vs. Forward Voltage  $V_F$

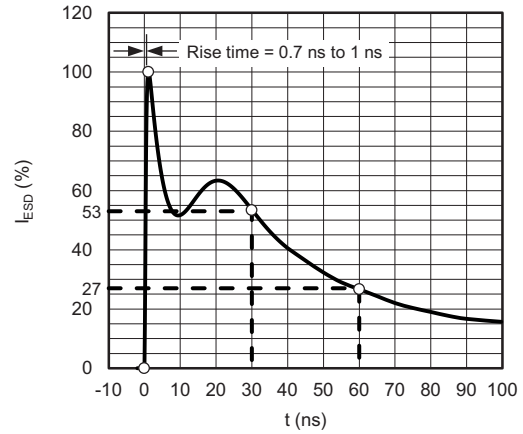


Fig. 4 - ESD Discharge Current Waveform According to IEC 61000-4-2 (330  $\Omega$  / 150 pF)

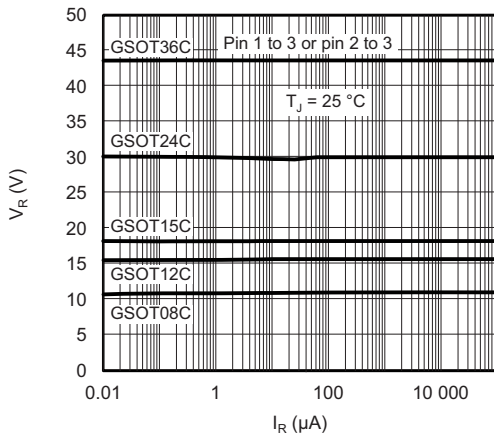


Fig. 2 - Typical Reverse Voltage  $V_R$  vs. Reverse Current  $I_R$

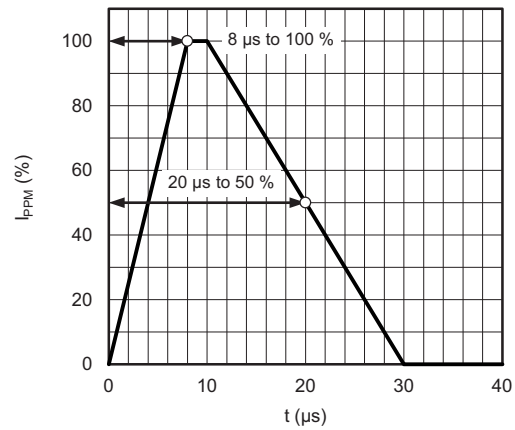


Fig. 5 - 8/20  $\mu$ s Peak Pulse Current Waveform According to IEC 61000-4-5

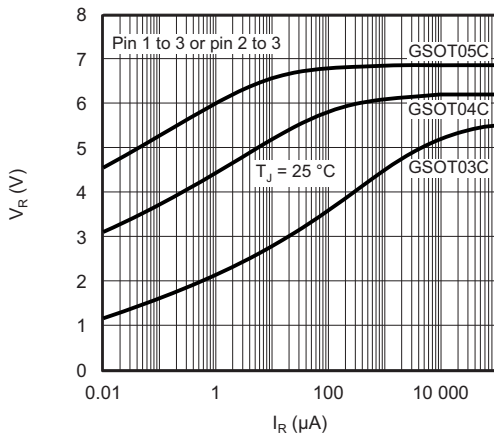


Fig. 3 - Typical Reverse Voltage  $V_R$  vs. Reverse Current  $I_R$

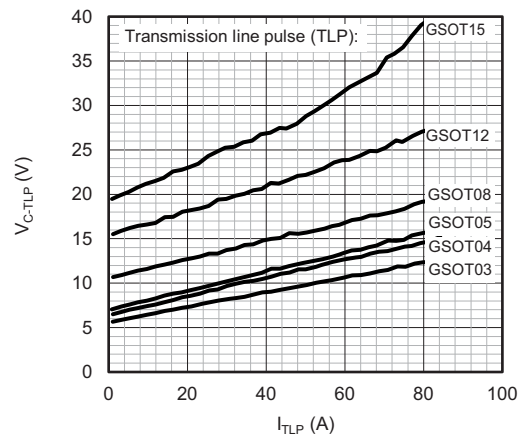


Fig. 6 - Typical Clamping Voltage vs. Peak Pulse Current

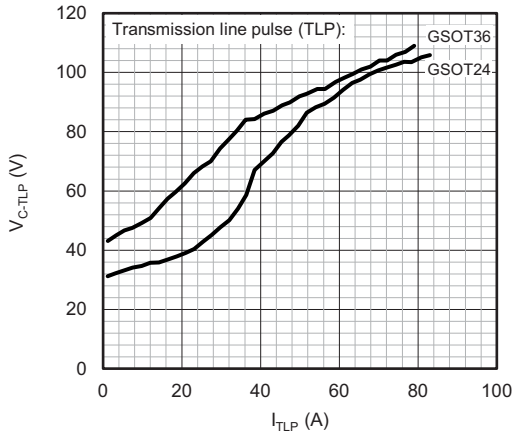


Fig. 7 - Typical Clamping Voltage vs. Peak Pulse Current

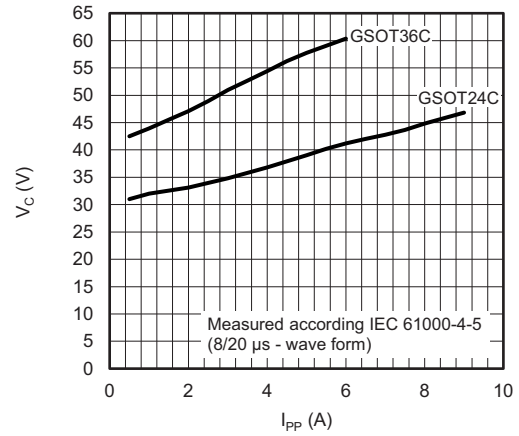


Fig. 9 - Typical Peak Clamping Voltage vs. Peak Pulse Current

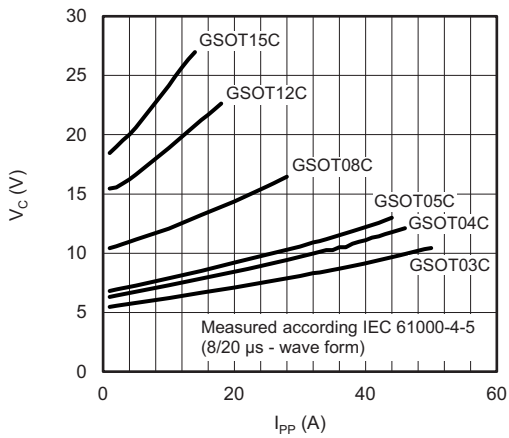


Fig. 8 - Typical Peak Clamping Voltage vs. Peak Pulse Current

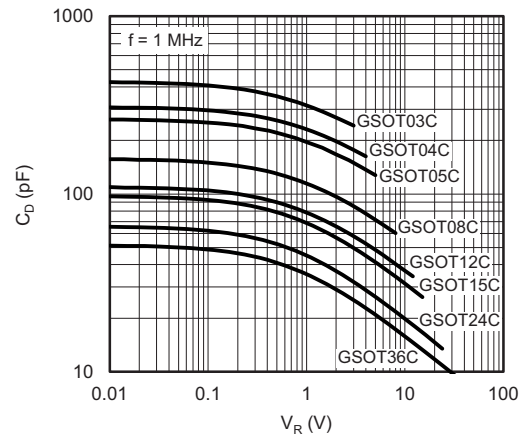
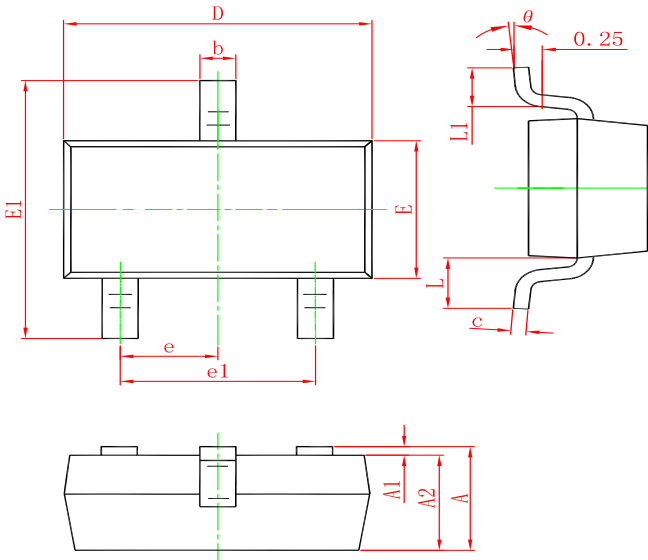


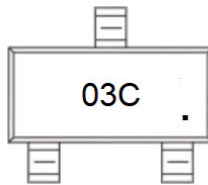
Fig. 10 - Typical Capacitance vs. Reverse Voltage

**SOT-23 PACKAGE OUTLINE DIMENSIONS**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

**Marking**



**Ordering information**

Order code	Package	Baseqty	Deliverymode	Marking
UMW GSOT03C-E3-08	SOT-23	3000	Tape and reel	03C
UMW GSOT04C-E3-08	SOT-23	3000	Tape and reel	04C
UMW GSOT05C-E3-08	SOT-23	3000	Tape and reel	05C
UMW GSOT08C-E3-08	SOT-23	3000	Tape and reel	08C
UMW GSOT12C-E3-08	SOT-23	3000	Tape and reel	12C
UMW GSOT15C-E3-08	SOT-23	3000	Tape and reel	15C
UMW GSOT24C-E3-08	SOT-23	3000	Tape and reel	24C
UMW GSOT36C-E3-08	SOT-23	3000	Tape and reel	36C

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